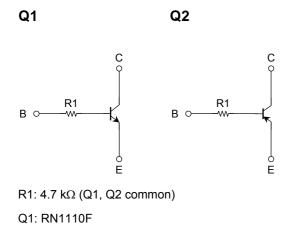
TOSHIBA Transistor Silicon NPN · PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

RN47A1

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Ultra-Super-Mini (5 pin) • package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.

Equivalent Circuit and Bias Resistor Values

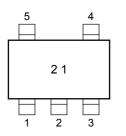


 2.1 ± 0.1 1.25 ± 0.1 0.65 2.0±0.2 1.3±0.1 ~°° 0.15±0.05 0.9±0.0 °~0 1. EMITTER 1 2. BASE 1 (E1) (B1) 3. EMITTER 2 (E2) 4. COLLECTOR 2 5. COLLECTOR 1 (C2) (C1) BASE 2 USV (B2) JEDEC _ JEITA TOSHIBA _

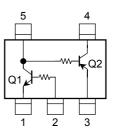
g (typ.)

Marking

Q2: RN2110F



Equivalent Circuit (top view)



Weight:

Unit: mm

Maximum Ratings (Ta = 25°C) (Q1)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ι _C	100	mA

Maximum Ratings (Ta = 25°C) (Q2)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	۱ _С	-100	mA

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P _C (Note)	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Note: Total rating

Electrical Characteristics (Ta = 25°C) (Q1)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB}=50~V,~I_{E}=0$	_		100	nA
Emitter cut-off current	I _{EBO}	$V_{EB}=5~V,~I_C=0$			100	nA
DC current gain	h _{FE}	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$	120	_	700	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = 5 \text{ mA}, I_{B} = 0.25 \text{ mA}$	_	0.1	0.3	V
Transition frequency	f _T	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	_	250	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	3	6	pF
Input resistor	R1	—	3.29	4.7	6.11	kΩ

Electrical Characteristics (Ta = 25°C) (Q2)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$	_		-100	nA
Emitter cut-off current	I _{EBO}	$V_{EB}=-5~V,~I_C=0$	_	_	-100	nA
DC current gain	h _{FE}	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -1 \text{ mA}$	120	_	700	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = -5 \text{ mA}, I_{B} = -0.25 \text{ mA}$	_	-0.1	-0.3	V
Transition frequency	f _T	$V_{CE} = -10 \text{ V}, \text{ I}_{C} = -5 \text{ mA}$	_	250	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	3	6	pF
Input resistor	R1	—	3.29	4.7	6.11	kΩ

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